## 1. General description

NPN/PNP general-purpose double transistors in a leadless ultra small DFN1412-6 (SOT1268) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: BC847RA PNP/PNP complement: BC857RA

## 2. Features and benefits

- Reduces component count
- Reduces pick and place costs
- Low package height of 0.5 mm
- AEC-Q101 qualified

## 3. Applications

- · General-purpose switching and amplification
- · Mobile applications

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor;	Per transistor; for the PNP transistor with negative polarity							
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	45	V	
I <sub>C</sub>	collector current			-	-	100	mA	
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	200	mA	
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 5 V; $I_{C}$ = 2 mA; $T_{amb}$ = 25 °C		200	-	450		



### 45 V, 100 mA NPN/PNP general-purpose double transistors

## 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		6 5 4
2	B1	base TR1	7 6	
3	C2	collector TR2	2 5	(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2	3 8 4	1 2 3
6	C1	collector TR1		sym019
7	C1	collector TR1	Transparent top view	
8	C2	collector TR2	DFN1412-6 (SOT1268)	

## 6. Ordering information

**Table 3. Ordering information** 

Type number	Package					
	Name	Description	Version			
BC847RAPN	DFN1412-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 mm x 1.2 mm x 0.47 mm	SOT1268			

## 7. Marking

#### **Table 4. Marking codes**

Type number	Marking code
BC847RAPN	A4

### 45 V, 100 mA NPN/PNP general-purpose double transistors

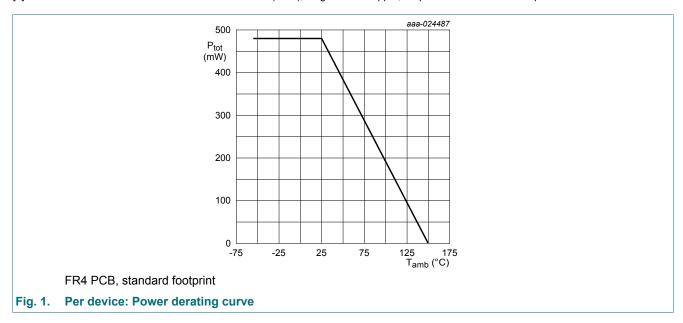
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or; for the PNP transistor wit	h negative polarity	•			
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
$V_{CEO}$	collector-emitter voltage	open base		-	45	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	200	mA
I <sub>BM</sub>	peak base current			-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	325	mW
Per device			,	'		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	480	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



#### 45 V, 100 mA NPN/PNP general-purpose double transistors

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	261	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

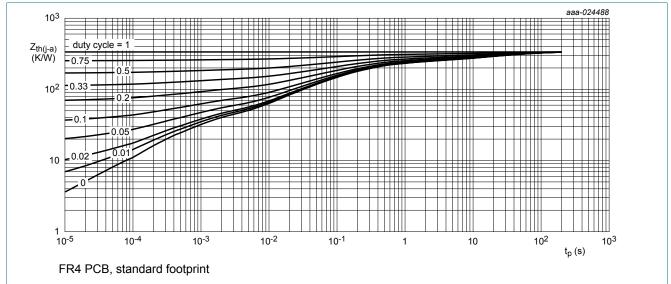


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 45 V, 100 mA NPN/PNP general-purpose double transistors

## 10. Characteristics

**Table 7. Characteristics** 

	Conditions	Min	Тур	Max	Unit
or the PNP transistor <b>v</b>	vith negative polarity				
collector-base cut-off	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	15	nA
current	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	5	μΑ
emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	200	-	450	
collector-emitter	$I_C$ = 10 mA; $I_B$ = 0.5 mA; $T_{amb}$ = 25 °C	-		100	mV
saturation voltage	$I_C$ = 100 mA; $I_B$ = 5 mA; $T_{amb}$ = 25 °C	-	-	300	mV
base-emitter saturation voltage	$I_C$ = 10 mA; $I_B$ = 0.5 mA; $T_{amb}$ = 25 °C	-	760	-	mV
	$I_C$ = 100 mA; $I_B$ = 5 mA; $T_{amb}$ = 25 °C	-	900	-	mV
base-emitter voltage	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	600	660	725	mV
	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; $T_{amb}$ = 25 °C	-	710	820	mV
collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	-	4	pF
emitter capacitance	$V_{EB}$ = 0.5 V; $I_{C}$ = 0 A; $I_{c}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	11	-	pF
	$V_{EB}$ = -0.5 V; $I_{C}$ = 0 mA; $I_{c}$ = 0 mA; f = 1 MHz; $T_{amb}$ = 25 °C	-	10	-	pF
ransition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
noise figure	$V_{CE}$ = 5 V; $I_{C}$ = 0.2 mA; $R_{S}$ = 2 k $\Omega$ ; f = 1 MHz; $T_{amb}$ = 25 °C	-	-	10	dB
	collector-base cut-off current committer-base cut-off current collector-emitter caturation voltage collector capacitance collector capacitance committer capacitance consistency consisten	collector-base cut-off current $V_{CB} = 30 \text{ V}; \ I_E = 0 \text{ A}; \ T_{amb} = 25 ^{\circ}\text{C}$ $V_{CB} = 30 \text{ V}; \ I_E = 0 \text{ A}; \ T_{j} = 150 ^{\circ}\text{C}$ $V_{CB} = 30 \text{ V}; \ I_C = 0 \text{ A}; \ T_{amb} = 25 ^{\circ}\text{C}$ $V_{CB} = 5 \text{ V}; \ I_C = 0 \text{ A}; \ T_{amb} = 25 ^{\circ}\text{C}$ $V_{CB} = 5 \text{ V}; \ I_C = 2 \text{ mA}; \ T_{amb} = 25 ^{\circ}\text{C}$ $V_{CB} = 5 \text{ V}; \ I_C = 2 \text{ mA}; \ T_{amb} = 25 ^{\circ}\text{C}$ $V_{CB} = 10 \text{ mA}; \ I_B = 0.5 \text{ mA}; \ T_{amb} = 25 ^{\circ}\text{C}$ $V_{CB} = 10 \text{ mA}; \ I_B = 0.5 \text{ mA}; \ T_{amb} = 25 ^{\circ}\text{C}$ $V_{CB} = 10 \text{ mA}; \ I_B = 5 \text{ mA}; \ T_{amb} = 25 ^{\circ}\text{C}$ $V_{CB} = 5 \text{ V}; \ I_C = 2 \text{ mA}; \ T_{amb} = 25 ^{\circ}\text{C}$ $V_{CB} = 5 \text{ V}; \ I_C = 2 \text{ mA}; \ T_{amb} = 25 ^{\circ}\text{C}$ $V_{CB} = 10 \text{ V}; \ I_C = 10 \text{ mA}; \ T_{amb} = 25 ^{\circ}\text{C}$ collector capacitance $V_{CB} = 10 \text{ V}; \ I_C = 0 \text{ A}; \ I_C = 0 \text{ MA}; \ I_$	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C   - V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C   - V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C   - V <sub>CB</sub> = 30 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C   - V <sub>CB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C   - V <sub>CB</sub> = 5 V; I <sub>C</sub> = 2 mA; T <sub>amb</sub> = 25 °C   - V <sub>CB</sub> = 10 mA; I <sub>B</sub> = 0.5 mA; T <sub>amb</sub> = 25 °C   - V <sub>CB</sub> = 100 mA; I <sub>B</sub> = 0.5 mA; T <sub>amb</sub> = 25 °C   - V <sub>CB</sub> = 100 mA; I <sub>B</sub> = 0.5 mA; T <sub>amb</sub> = 25 °C   - V <sub>CB</sub> = 5 V; I <sub>C</sub> = 2 mA; T <sub>amb</sub> = 25 °C   - V <sub>CB</sub> = 5 V; I <sub>C</sub> = 10 mA; I <sub>D</sub> = 0 A; T <sub>amb</sub> = 25 °C   - V <sub>CB</sub> = 5 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C   - V <sub>CB</sub> = 10 V; I <sub>D</sub> = 10 mA; T <sub>amb</sub> = 25 °C   - V <sub>CB</sub> = 10 V; I <sub>D</sub> = 0 A;	$ \begin{array}{c} \text{collector-base cut-off} \\ \text{current} \\ \end{array} \begin{array}{c} V_{CB} = 30 \text{ V}; \ I_E = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \begin{array}{c} - \\ - \\ \text{current} \\ \end{array} \\ \begin{array}{c} V_{CB} = 30 \text{ V}; \ I_E = 0 \text{ A}; \ T_{j} = 150 \text{ °C} \\ \end{array} \\ - \\ - \\ \text{current} \\ \end{array} \\ \begin{array}{c} P_{CD} = 30 \text{ V}; \ I_C = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 30 \text{ V}; \ I_C = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 30 \text{ V}; \ I_C = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 30 \text{ V}; \ I_C = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 30 \text{ V}; \ I_C = 0 \text{ A}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 30 \text{ V}; \ I_C = 2 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 30 \text{ V}; \ I_C = 2 \text{ mA}; \ T_{amb} = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 30 \text{ V}; \ I_C = 10 \text{ mA}; \ I_D = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 100 \text{ mA}; \ I_D = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 100 \text{ mA}; \ I_D = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 100 \text{ mA}; \ I_D = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 100 \text{ mA}; \ I_D = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 100 \text{ mA}; \ I_D = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 10 \text{ mA}; \ I_D = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 10 \text{ mA}; \ I_D = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 10 \text{ mA}; \ I_D = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 10 \text{ mA}; \ I_D = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 10 \text{ mA}; \ I_D = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 10 \text{ mA}; \ I_D = 25 \text{ °C} \\ \end{array} \\ \begin{array}{c} P_{CD} = 10 \text{ mA}; \ I_D = 10 \text{ ma}; $	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C   -   -   5   5   5   5   5   5   5   5

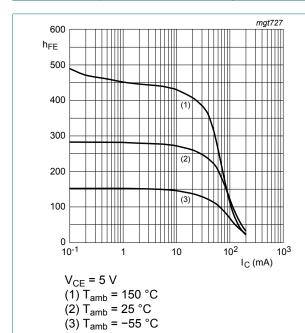


Fig. 3. NPN transistor: DC current gain as a function of collector current; typical values

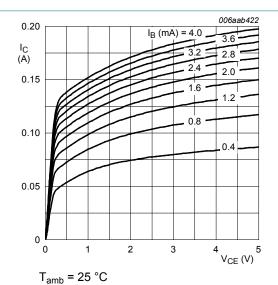
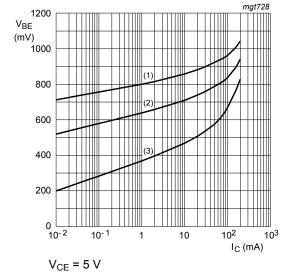


Fig. 4. NPN transistor: Collector current as a function of collector-emitter voltage; typical values

#### 45 V, 100 mA NPN/PNP general-purpose double transistors



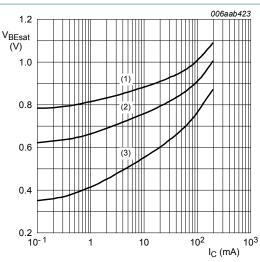
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \,^{\circ}\text{C}$$
  
(3)  $T_{amb} = 150 \,^{\circ}\text{C}$ 

Fig. 5. NPN transistor: Base-emitter voltage as a function of collector current; typical values



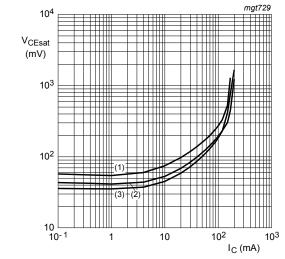
$$I_{\rm C}/I_{\rm B} = 20$$

$$(1) T_{amb} = -55 ° ($$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$\begin{split} &I_{\text{C}}/I_{\text{B}} = 20\\ &(1)~T_{\text{amb}} = -55~^{\circ}\text{C}\\ &(2)~T_{\text{amb}} = 25~^{\circ}\text{C}\\ &(3)~T_{\text{amb}} = 150~^{\circ}\text{C} \end{split}$$

Fig. 6. NPN transistor: Base-emitter saturation voltage as a function of collector current; typical values



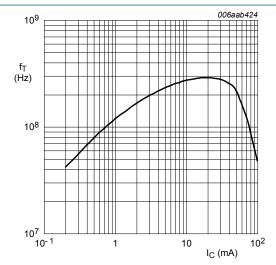
$$I_C/I_B = 20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

**NPN** transistor: Collector-emitter saturation Fig. 7. voltage as a function of collector current; typical values

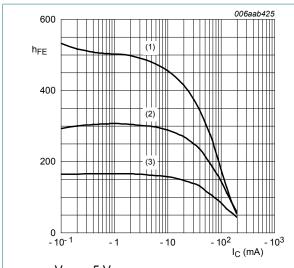


$$T_{amb} = 25 \,^{\circ}C;$$

$$V_{CE} = 5 V;$$
  
f = 100 MHz

NPN transistor: Transition frequency as a Fig. 8. function of collector current; typical values

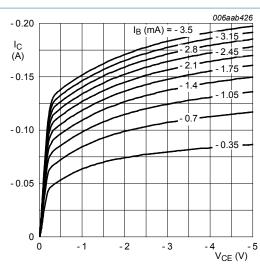
#### 45 V, 100 mA NPN/PNP general-purpose double transistors



 $V_{CE}$  = -5 V

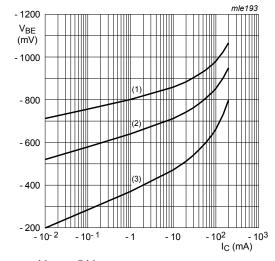
(1) T<sub>amb</sub> = 150 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -55 °C

Fig. 9. PNP transistor: DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig. 10. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



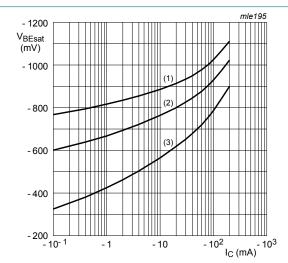
 $V_{CE}$  = -5 V

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig. 11. PNP transistor: Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig. 12. PNP transistor: Base-emitter saturation voltage as a function of collector current; typical values

#### 45 V, 100 mA NPN/PNP general-purpose double transistors

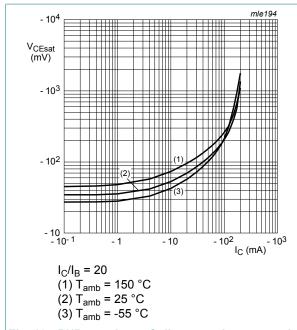


Fig. 13. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values

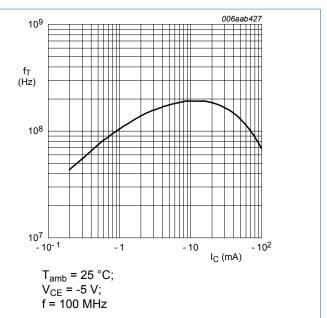


Fig. 14. PNP transistor: Transition frequency as a function of collector current; typical values

## 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### 45 V, 100 mA NPN/PNP general-purpose double transistors

## 12. Package outline

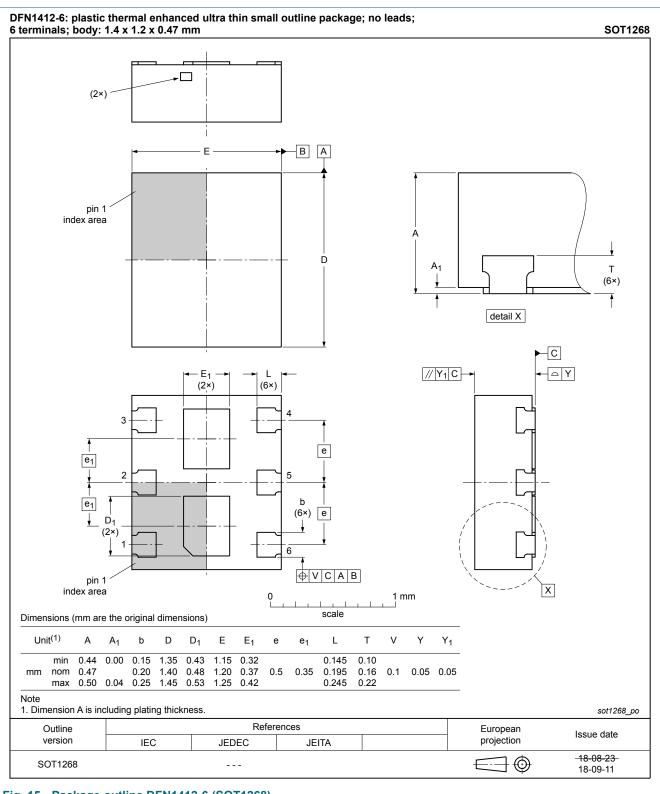
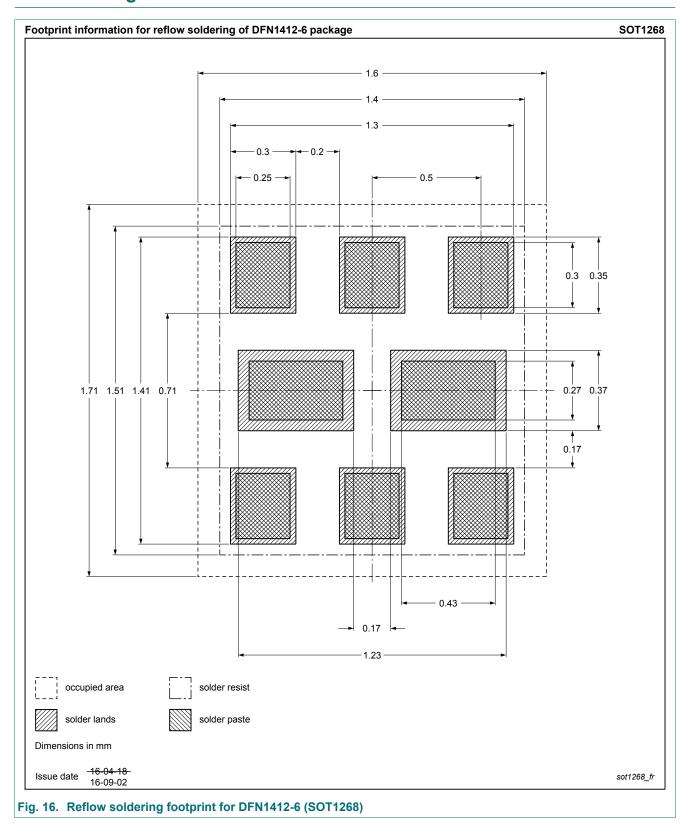


Fig. 15. Package outline DFN1412-6 (SOT1268)

### 45 V, 100 mA NPN/PNP general-purpose double transistors

## 13. Soldering



### 45 V, 100 mA NPN/PNP general-purpose double transistors

# 14. Revision history

#### Table 8. Revision history

······································								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
BC847RAPN v.2	20180914	Product data sheet	-	BC847RAPN v.1				
Modifications:	Package outline d	Package outline drawing updated: Unit T added						
BC847RAPN v.1	20170607	Product data sheet	-	-				

#### 45 V, 100 mA NPN/PNP general-purpose double transistors

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <a href="https://www.nexperia.com">https://www.nexperia.com</a>.

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### 45 V, 100 mA NPN/PNP general-purpose double transistors

## **Contents**

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	4
10.	Characteristics	5
11.	Test information	8
12.	Package outline	9
13.	Soldering	10
14.	Revision history	11
	Legal information	

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